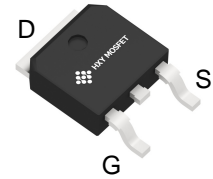




## Description

The IPD047N03LF2SATMA1 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO-252-2L

## General Features

$V_{DS} = 30V$   $I_D = 100A$

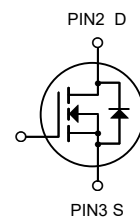
$R_{DS(ON)} < 5.5m\Omega @ V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

## Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD047N03LF2SATMA1	TO-252-2L	HXY MOSFET	2500

## Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain- Source Voltage	30	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D@Tc=25°C</sub>	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	100	A	
I <sub>D@Tc=100°C</sub>	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	57	A	
I <sub>D@TA=25°C</sub>	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	27	17	A
I <sub>D@TA=70°C</sub>	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	23	14.5	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	160	A	
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>3</sup>	115.2	mJ	
I <sub>AS</sub>	Avalanche Current	48	A	
P <sub>D@Tc=25°C</sub>	Total Power Dissipation <sup>4</sup>	53	W	
P <sub>D@TA=25°C</sub>	Total Power Dissipation <sup>4</sup>	6	2.4	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 175	°C	
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 175	°C	
R <sub>θJA</sub>	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	62	°C/W	
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤10s)	25	°C/W	
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	2.8	°C/W	



**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.028	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	3.8	5.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	7.5	9	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.5	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-6.16	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =30A	---	22	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.7	3.4	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	20	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	7.6	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	7.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3, I <sub>D</sub> =15A	---	7.8	---	ns
T <sub>r</sub>	Rise Time		---	15	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	37.3	---	
T <sub>f</sub>	Fall Time		---	10.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	2295	---	pF
C <sub>oss</sub>	Output Capacitance		---	267	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	210	---	
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	80	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	160	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =30A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	14	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	5	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3.The test cond<sub>≤</sub> 300us , duty cycle ition is V<sub>DD=25</sub>≤V, V 2%<sub>GS</sub> =10V, L=0.1mH, I<sub>AS</sub>=53.8A
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.



### Typical Characteristics

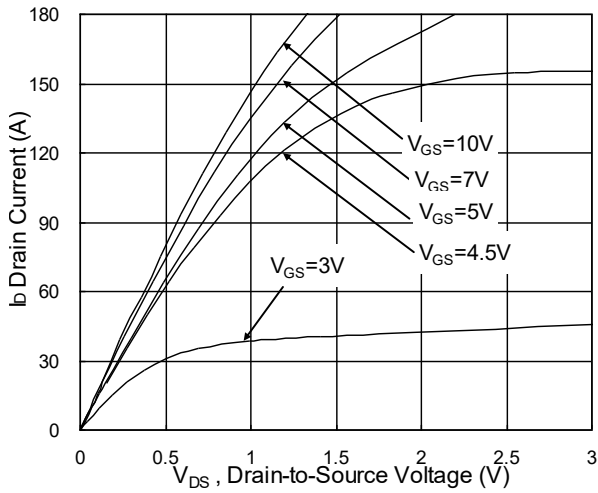


Fig.1 Typical Output Characteristics

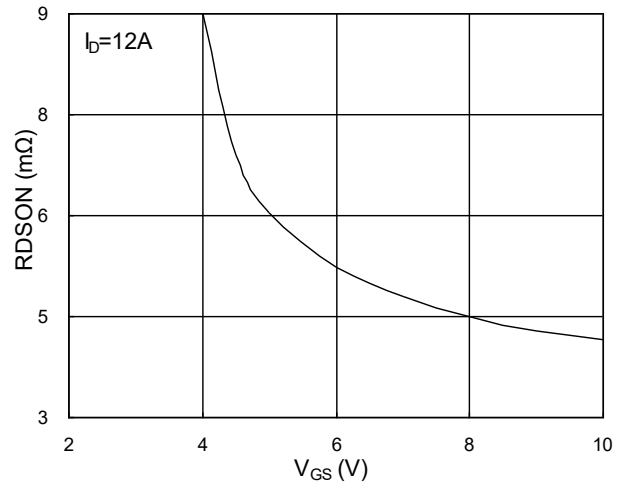


Fig.2 On-Resistance vs. G-S Voltage

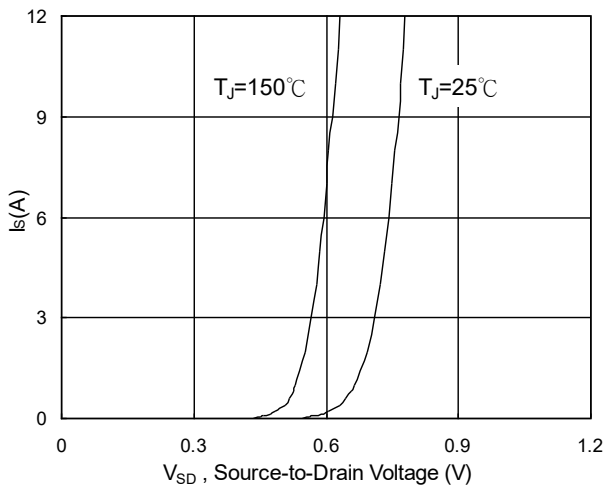


Fig.3 Forward Characteristics of Reverse

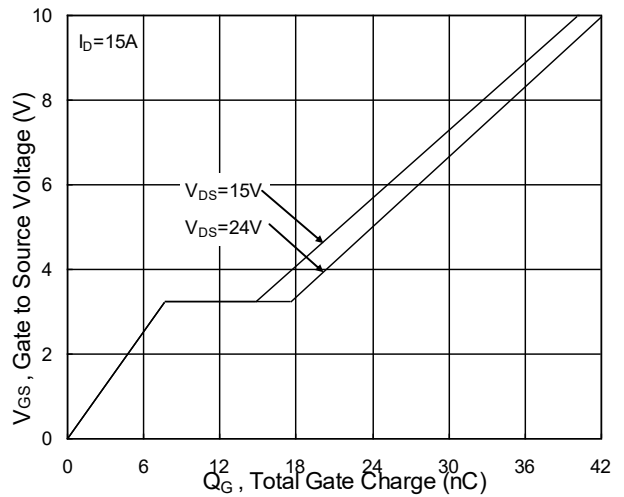


Fig.4 Gate-Charge Characteristics

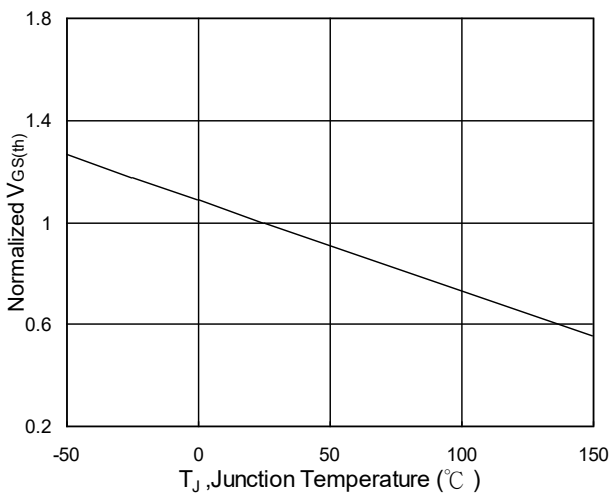


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

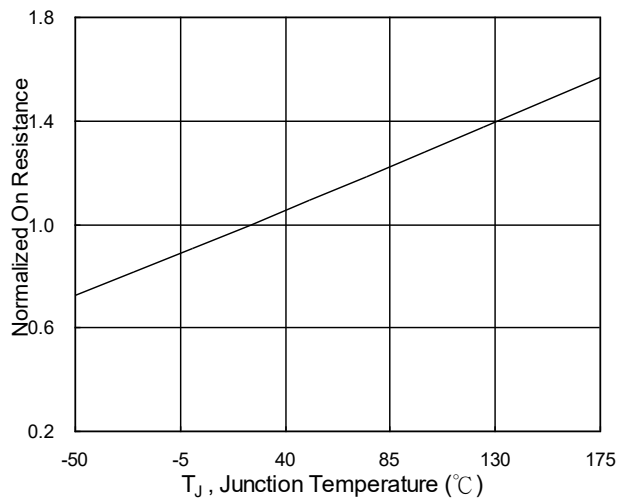


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

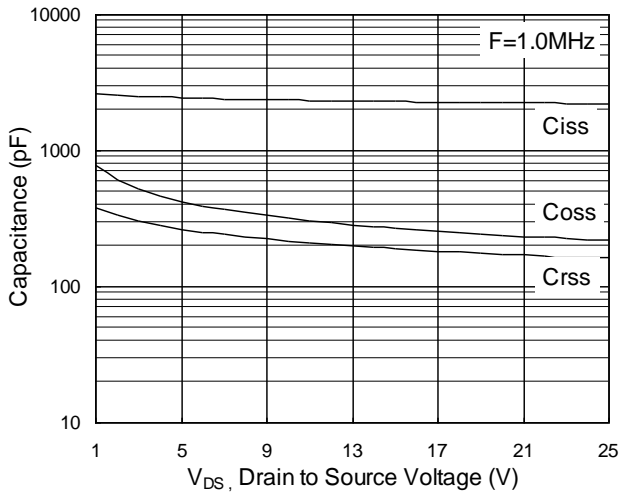


Fig.7 Capacitance

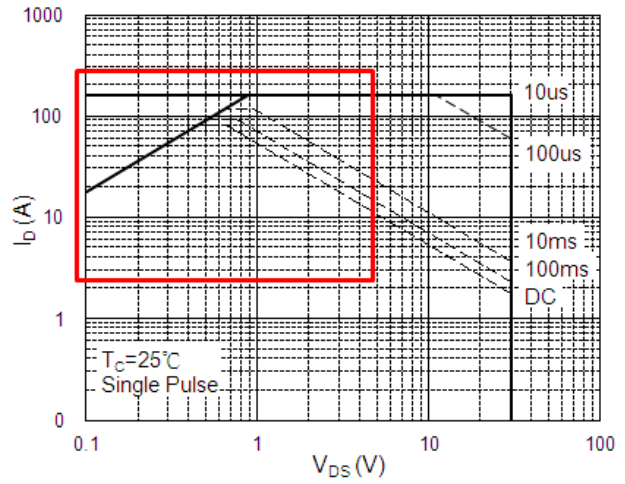


Fig.8 Safe Operating Area

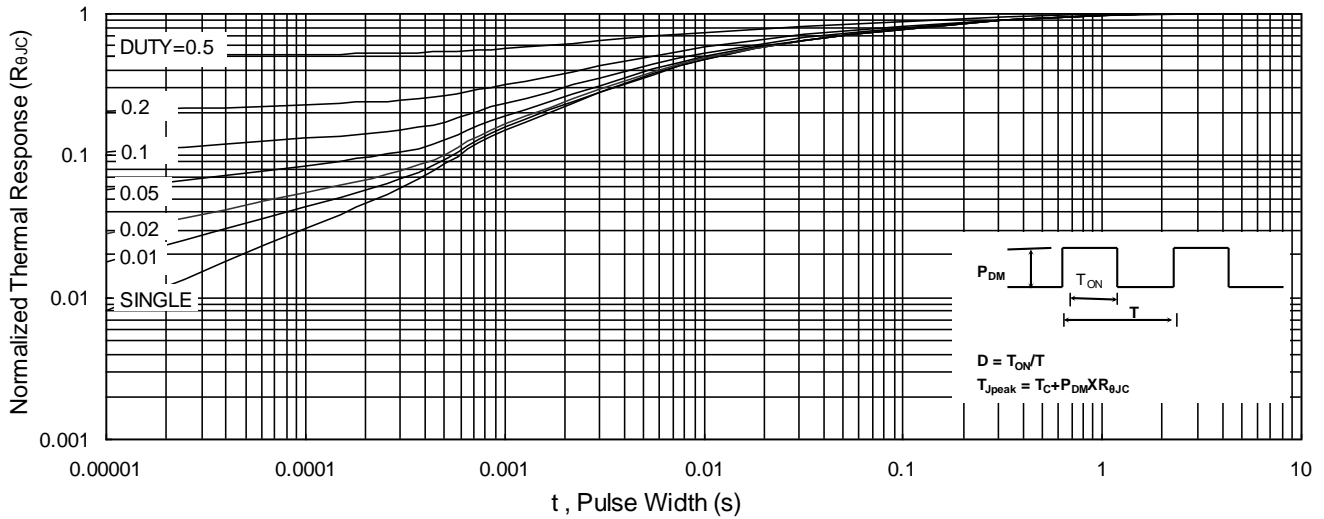


Fig.9 Normalized Maximum Transient Thermal Impedance

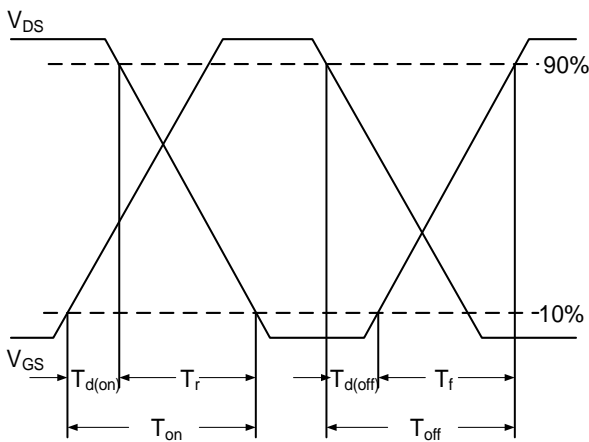


Fig.10 Switching Time Waveform

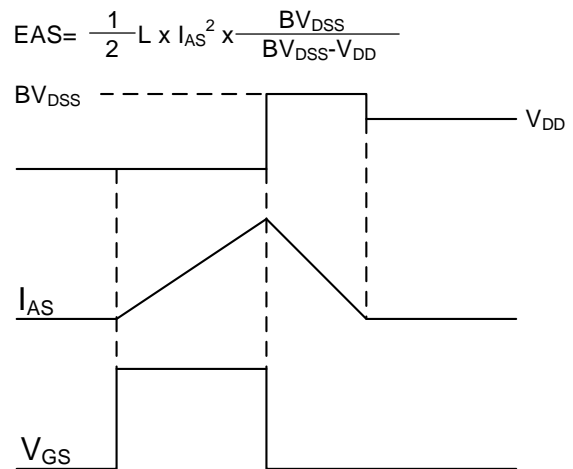


Fig.11 Unclamped Inductive Switching Waveform





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